

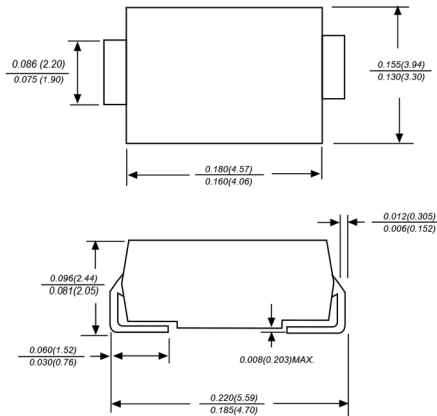
## FEATURES

- Metal-Semiconductor junction with gard ring
- Epitaxial construction
- Low forward voltage drop
- High current capability
- The plastic material carries UL recognition 94V-0
- For use in low vlotage, high frequency inverters, free wheeling, and polarity protection applications

## MECHANICAL DATA

- Case: Molded Plastic
- Polarity: Color band denotes cathode
- Weight :0.09 grams

**DO-214AA**



## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.  
Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

| CHARACTERISTICS   | SYMBOL                         | SS52        | SS53 | SS54 | SS55 | SS56 | SS58 | SS510 | SS515 | SS520 | UNIT |
|---|--------------------------------|-------------|------|------|------|------|------|-------|-------|-------|------|
| Maximum Recurrent Peak Reverse Voltage  | V <sub>RRM</sub>               | 20          | 30   | 40   | 50   | 60   | 80   | 100   | 150   | 200   | V    |
| Maximum RMS Voltage   | V <sub>RMS</sub>               | 14          | 21   | 28   | 35   | 42   | 56   | 70    | 105   | 140   | V    |
| Maximum DC Blocking Voltage   | V <sub>DC</sub>                | 20          | 30   | 40   | 50   | 60   | 80   | 100   | 150   | 200   | V    |
| Maximum Average Forward Rectified Current<br>0.375" (9.5mm) Lead Lengths                                | I <sub(av)< sub=""></sub(av)<> | 5.0         |      |      |      |      |      |       |       |       | A    |
| Peak Forward Surge Current<br>8.3ms Single Half Sine-Wave<br>Super Imposed on Rated Load(JEDEC Method)  | I <sub>FSM</sub>               | 100         |      |      |      |      |      |       |       |       | A    |
| Maximum Forward Voltage at 5.0A DC  | V <sub>F</sub>                 | 0.55        |      |      | 0.7  |      | 0.85 |       | 0.95  |       | V    |
| Maximum DC Reverse Current @T <sub>J</sub> =25°C<br>at Rated DC Bolcking Voltage @T <sub>J</sub> =100°C | I <sub>R</sub>                 | 0.2         |      |      | 50   |      | 1.0  |       | 50    |       | mA   |
| Typical Junction Capacitance (Note1)  | C <sub>J</sub>                 | 500         |      |      | 350  |      | 350  |       | 350   |       | pF   |
| Typical Thermal Resistance (Note2)  | R <sub>θJA</sub>               | 15          |      |      | 10   |      | 10   |       | 10    |       | °C/W |
| Operating Temperature Range   | T <sub>J</sub>                 | -55 to +150 |      |      |      |      |      |       |       |       | °C   |
| Storage Temperature Range   | T <sub>STG</sub>               | -55 to +150 |      |      |      |      |      |       |       |       | °C   |

NOTES: 1. Measured at 1.0 MHz and applied reverse voltage of 4.0V DC

2. Thermal resistance junction to ambient,

FIG. 1 – FORWARD CURRENT DERATING CURVE

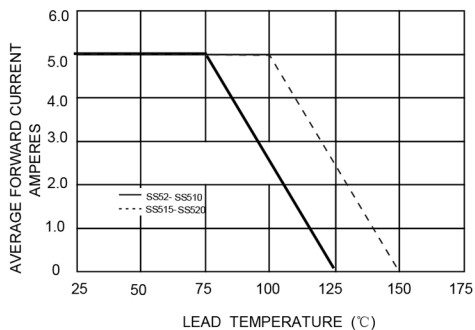


FIG. 2 – MAXIMUM NON-REPETITIVE SURGE CURRENT

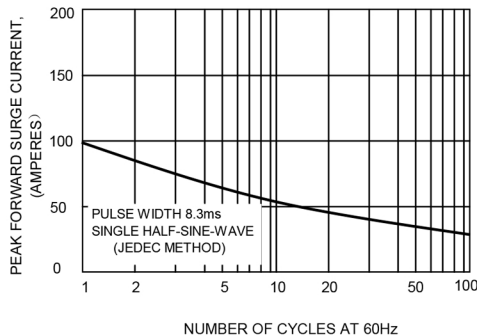


FIG. 3 – TYPICAL JUNCTION CAPACITANCE

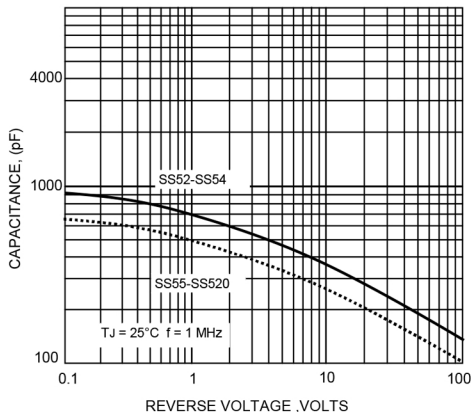


FIG. 4-TYPICAL FORWARD CHARACTERISTICS

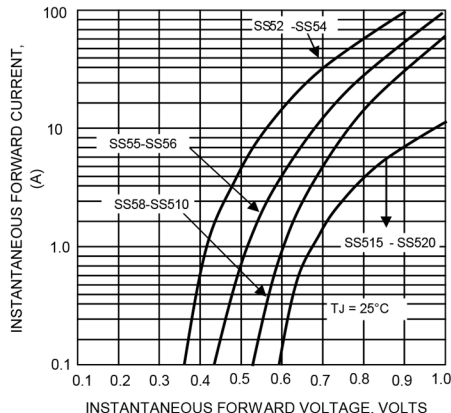
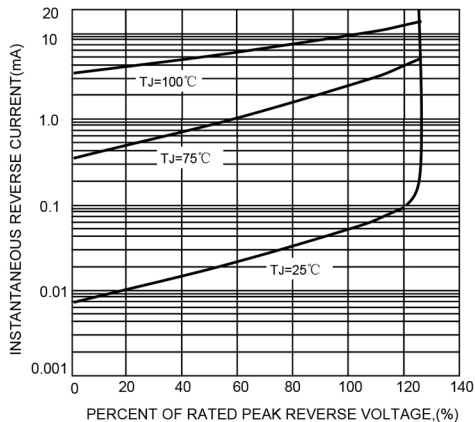


FIG. 2-TYPICAL REVER CHARACTERISTICS



单击下面可查看定价，库存，交付和生命周期等信息

[>>RCD\(达标电子\)](#)